

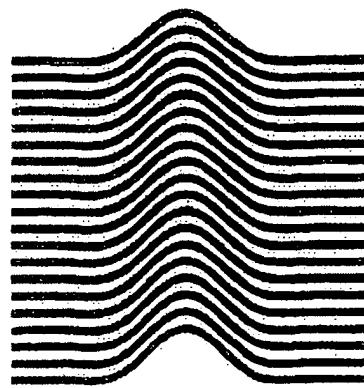
116

FIG. 1 A

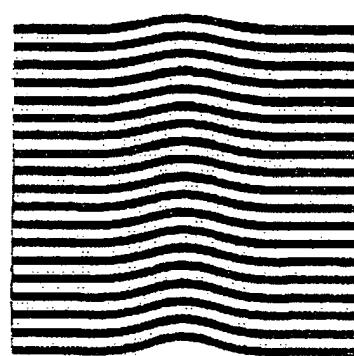
FIG. B

Focused Beam

(a)



(b)



10

卷之三

2/6

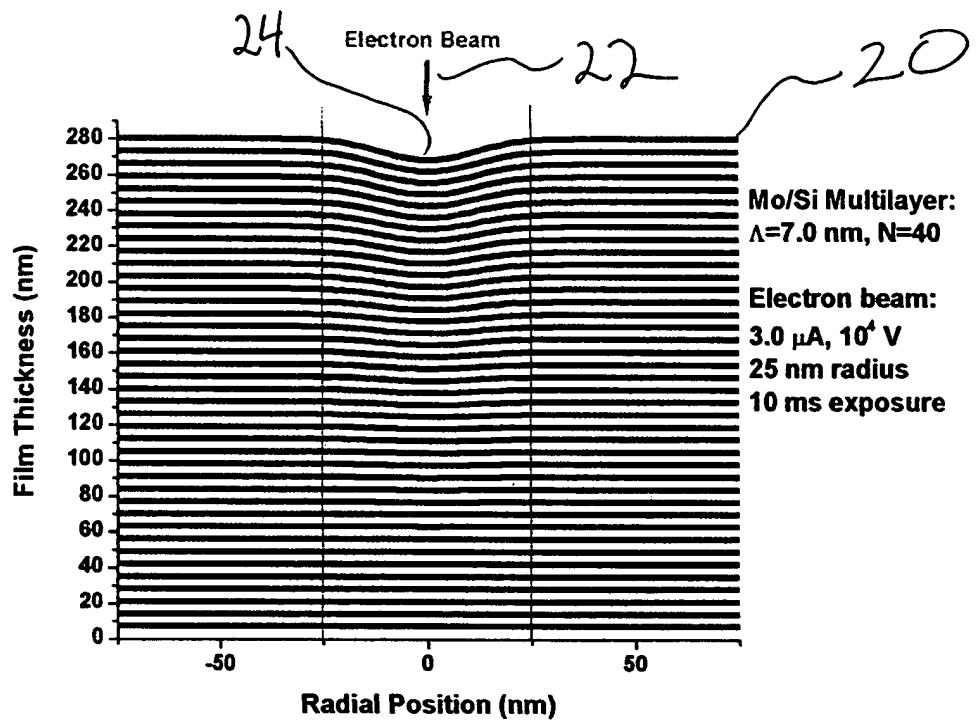


FIG. 2

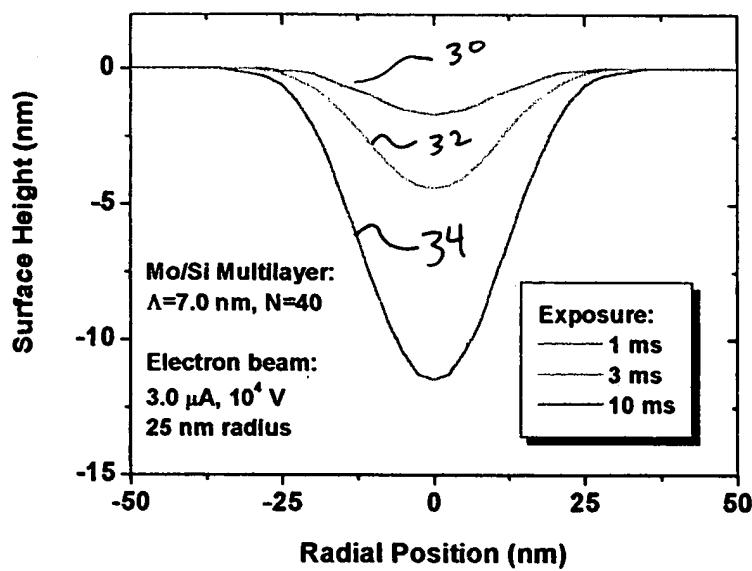


FIG. 3

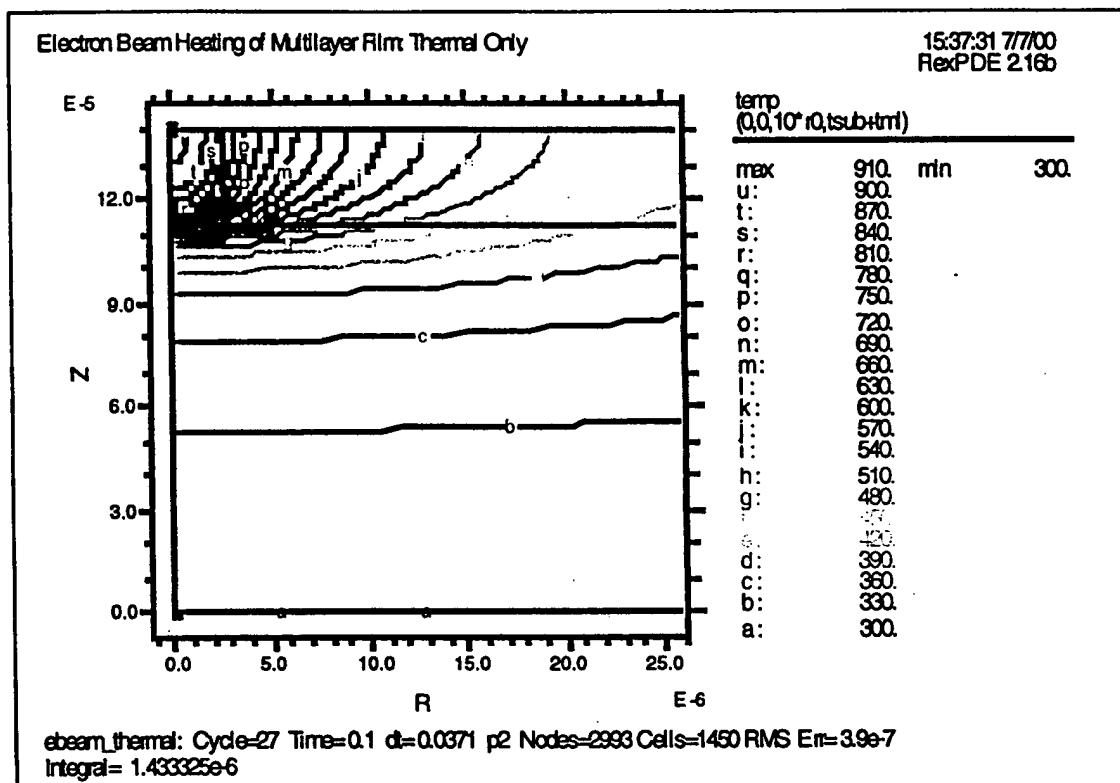


Figure 1 Temperature profile for a Mo/Si multilayer film on a Si substrate heated by an electron beam having a current and voltage of 3 μ A and 10 kV, respectively. The electron beam is incident on the top left corner and has a radius of 25 nm.

FIG. 4

5/6

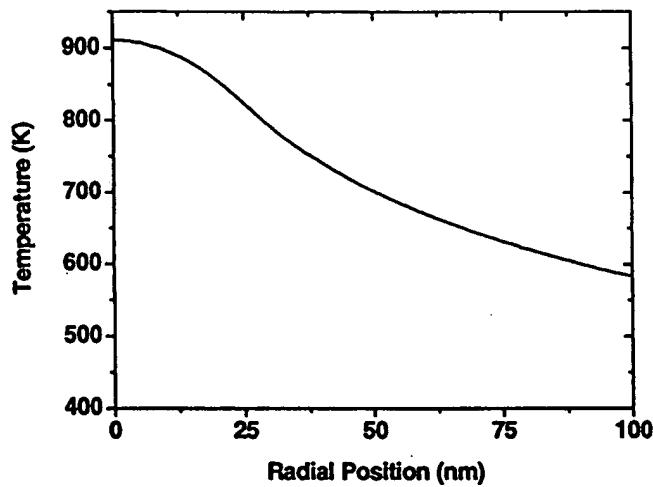


Figure 2 Temperature at the top surface ($z = 280$ nm) of the multilayer film as a function of radial position for heating via an electron beam.

FIG. 5

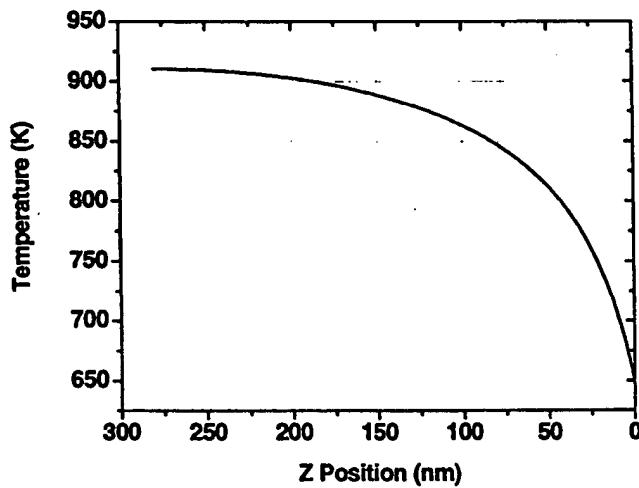


Figure 3 Temperature at the center of the electron beam ($r = 0$) as a function of depth in the multilayer film. The total thickness of the film is 280 nm.

FIG. 6

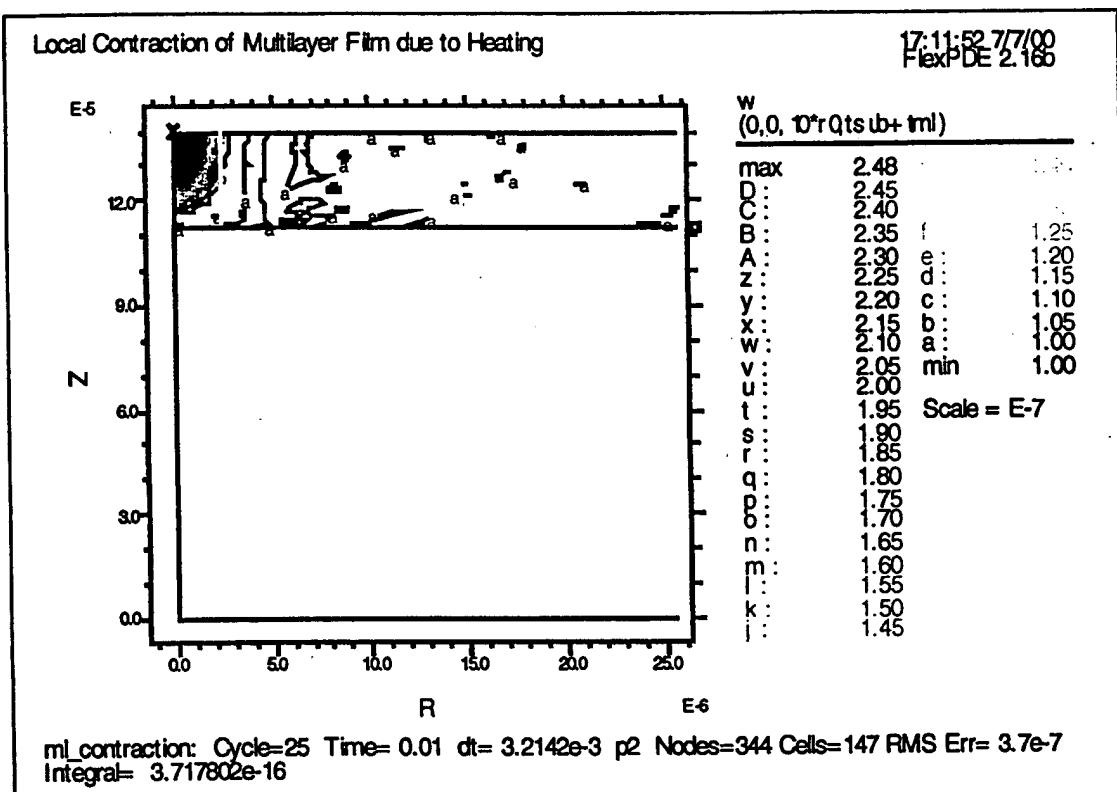


Figure 7 Contour plot showing the width w of the silicide interlayer within the Mo/Si multilayer film after an electron beam exposure of 10 ms. The width varies from the as-deposited value of $w_0 = 1.0$ nm to a maximum value of 2.48 nm in the center of the electron beam.

FIG. 7